Combined SIMS-SPM instrument for high sensitivity and high resolution elemental 3D analysis

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Owing in particular to its excellent sensitivity, its high dynamic range and its good depth resolution, Secondary Ion Mass Spectrometry (SIMS) constitutes an extremely powerful technique for analyzing surfaces and thin films. In recent years, considerable efforts have been spent to further improve the spatial resolution of SIMS instruments. As a consequence, new fields of application for SIMS, e.g. nanotechnologies, biology and medicine in particular, are emerging.

State-of-the-art SIMS instruments allow producing 3D chemical mappings with excellent sensitivity and spatial resolution. Several important artifacts however arise from the fact that the 3D mappings do not take into account the surface topography of the sample. The traditional 3D reconstruction assumes that the initial sample surface is flat and the analyzed volume is cuboid. The produced 3D images are thus affected by a more or less important uncertainty on the depth scale and can be distorted. The situation becomes even more complicated as the topography changes during the ion bombardment. Moreover, significant field inhomogeneities arise from the surface topography as a result of distortion of the local electric field. These perturb both the primary beam and the trajectories of secondary ions, resulting in a number of possible artifacts, including shifts in apparent pixel position and changes in intensity.

In order to obtain real high-resolution SIMS 3D analyses without being prone to the aforementioned artifacts and limitations, we have developed for the first time an integrated SIMS-SPM instrument. This instrument, which is based on the Cameca NanoSIMS 50, involves an in-situ combination of sequential high resolution Scanning Probe Microscopy (SPM) and high sensitivity SIMS. This prototype system allows topographical images of the sample surface to be recorded in-situ before, in between and after SIMS analysis. High-sensitivity high-resolution chemical 3D reconstructions become possible with this extremely powerful analytical tool.

This paper will present the prototype instrument, the dedicated software and some typical applications.

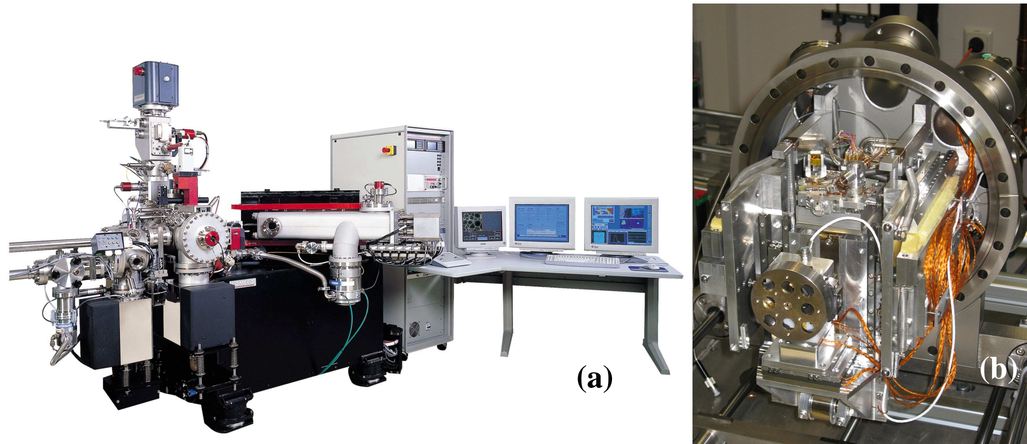

Figure 1: Photos of the prototype set-up: Cameca NanoSIMS 50 (a) and new high-precision sample stage with integrated SPM device (b).

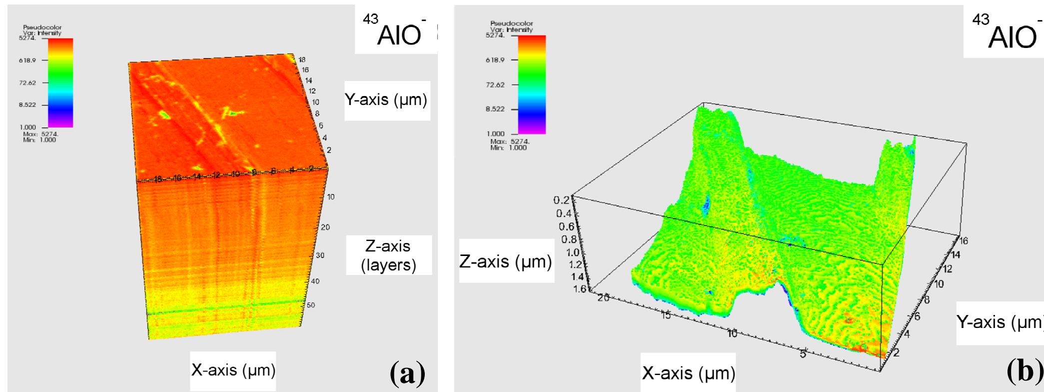

Figure 2: Al/Cu sample: (a) Traditional NanoSIMS 50 3D reconstruction of the $^{43}AlO^-$ secondary ion signal. Field of view: 20x20 µm^2. (b) Combined SIMS-SPM 3D reconstruction of the $^{43}AlO^-$ signal. Field of view: 22.3x17.3 µm^2.